

HD74HC01

Quad. 2-input NAND Gates (with open drain outputs)

REJ03D0532-0200
(Previous ADE-205-404)
Rev.2.00
Oct 06, 2005

Features

- High Speed Operation: $t_{pd} = 9 \text{ ns typ (} C_L = 50 \text{ pF)}$
- High Output Current: Fanout of 10 LSTTL Loads
- Wide Operating Voltage: $V_{CC} = 2 \text{ to } 6 \text{ V}$
- Low Input Current: $1 \mu\text{A max}$
- Low Quiescent Supply Current: $I_{CC} \text{ (static)} = 1 \mu\text{A max (} T_a = 25^\circ\text{C)}$
- Ordering Information

Part Name	Package Type	Package Code (Previous Code)	Package Abbreviation	Taping Abbreviation (Quantity)
HD74HC01P	DILP-14 pin	PRDP0014AB-B (DP-14AV)	P	—
HD74HC01FPEL	SOP-14 pin (JEITA)	PRSP0014DF-B (FP-14DAV)	FP	EL (2,000 pcs/reel)
HD74HC01RPEL	SOP-14 pin (JEDEC)	PRSP0014DE-A (FP-14DNV)	RP	EL (2,500 pcs/reel)

Note: Please consult the sales office for the above package availability.

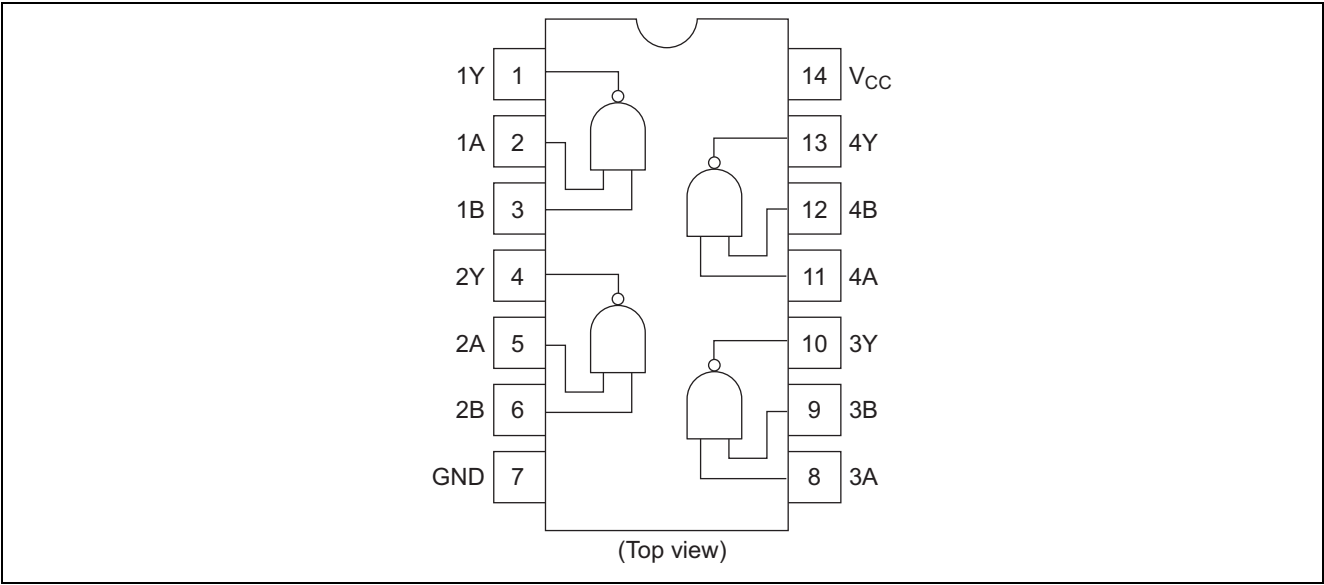
Function Table

Inputs		Output
A	B	Y
L	L	H
L	H	H
H	L	H
H	H	L

H : High level

L : Low level

[查询"HD74HC01"供应商](#)



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit
Supply voltage range	V _{CC}	−0.5 to 7.0	V
Input / Output voltage	V _{in} , V _{out}	−0.5 to V _{CC} +0.5	V
Input / Output diode current	I _{IK} , I _{OK}	±20	mA
Output current	I _O	±25	mA
V _{CC} , GND current	I _{CC} or I _{GND}	±50	mA
Power dissipation	P _T	500	mW
Storage temperature	T _{stg}	−65 to +150	°C

Note: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

Recommended Operating Conditions

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V _{CC}	2 to 6	V	
Input / Output voltage	V _{IN} , V _{OUT}	0 to V _{CC}	V	
Operating temperature	T _a	−40 to 85	°C	
Input rise / fall time ^{*1}	t _r , t _f	0 to 1000	ns	V _{CC} = 2.0 V
		0 to 500		V _{CC} = 4.5 V
		0 to 400		V _{CC} = 6.0 V

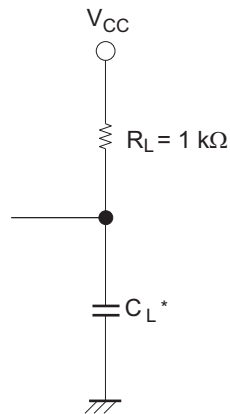
Note: 1. This item guarantees maximum limit when one input switches.
Waveform: Refer to test circuit of switching characteristics.

[Electrical Characteristics](#) [查看数据手册](#)

Item	Symbol	V _{CC} (V)	Ta = 25°C			Ta = -40 to +85°C		Unit	Test Conditions	
			Min	Typ	Max	Min	Max			
Input voltage	V _{IH}	2.0	1.5	—	—	1.5	—	V		
		4.5	3.15	—	—	3.15	—			
		6.0	4.2	—	—	4.2	—			
	V _{IL}	2.0	—	—	0.5	—	0.5	V		
		4.5	—	—	1.35	—	1.35			
		6.0	—	—	1.8	—	1.8			
Output voltage	V _{OL}	2.0	—	0.0	0.1	—	0.1	V	Vin = V _{IH} or V _{IL}	I _{OL} = 20 µA
		4.5	—	0.0	0.1	—	0.1			
		6.0	—	0.0	0.1	—	0.1			
		4.5	—	—	0.26	—	0.33			I _{OL} = 4 mA
		6.0	—	—	0.26	—	0.33			I _{OL} = 5.2 mA
Off-state output current	I _{O(off)}	6.0	—	—	±0.5	—	±5.0	µA	Vin = V _{IH} or V _{IL} , Vout = V _{CC} or GND	
Input current	I _{in}	6.0	—	—	±0.1	—	±1.0	µA	Vin = V _{CC} or GND	
Quiescent supply current	I _{CC}	6.0	—	—	1.0	—	10	µA	Vin = V _{CC} or GND, I _{out} = 0 µA	

Switching Characteristics (C_L = 50 pF, Input t_r = t_f = 6 ns)

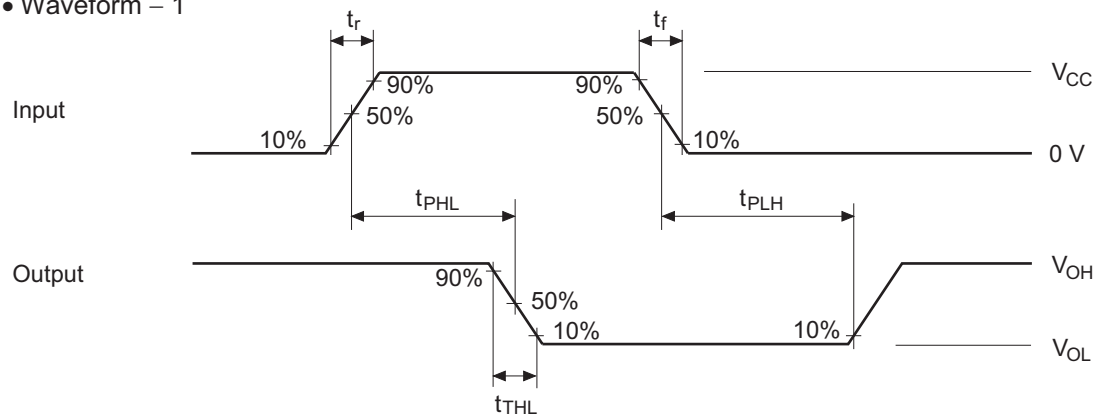
Item	Symbol	V _{CC} (V)	Ta = 25°C			Ta = -40 to +85°C		Unit	Test Conditions	
			Min	Typ	Max	Min	Max			
Propagation delay time	t _{PLH}	2.0	—	—	90	—	115	ns		
		4.5	—	11	18	—	23			
		6.0	—	—	15	—	20			
	t _{PHL}	2.0	—	—	90	—	112	ns		
		4.5	—	7	18	—	22			
		6.0	—	—	15	—	18			
Output fall time	t _{THL}	2.0	—	—	75	—	95	ns		
		4.5	—	5	15	—	19			
		6.0	—	—	13	—	16			
Input capacitance	C _{in}	—	—	5	10	—	10	pF		

[查看"HD74HC01RPEL"供应商](#)


Note: C_L includes the probe and jig capacitance.

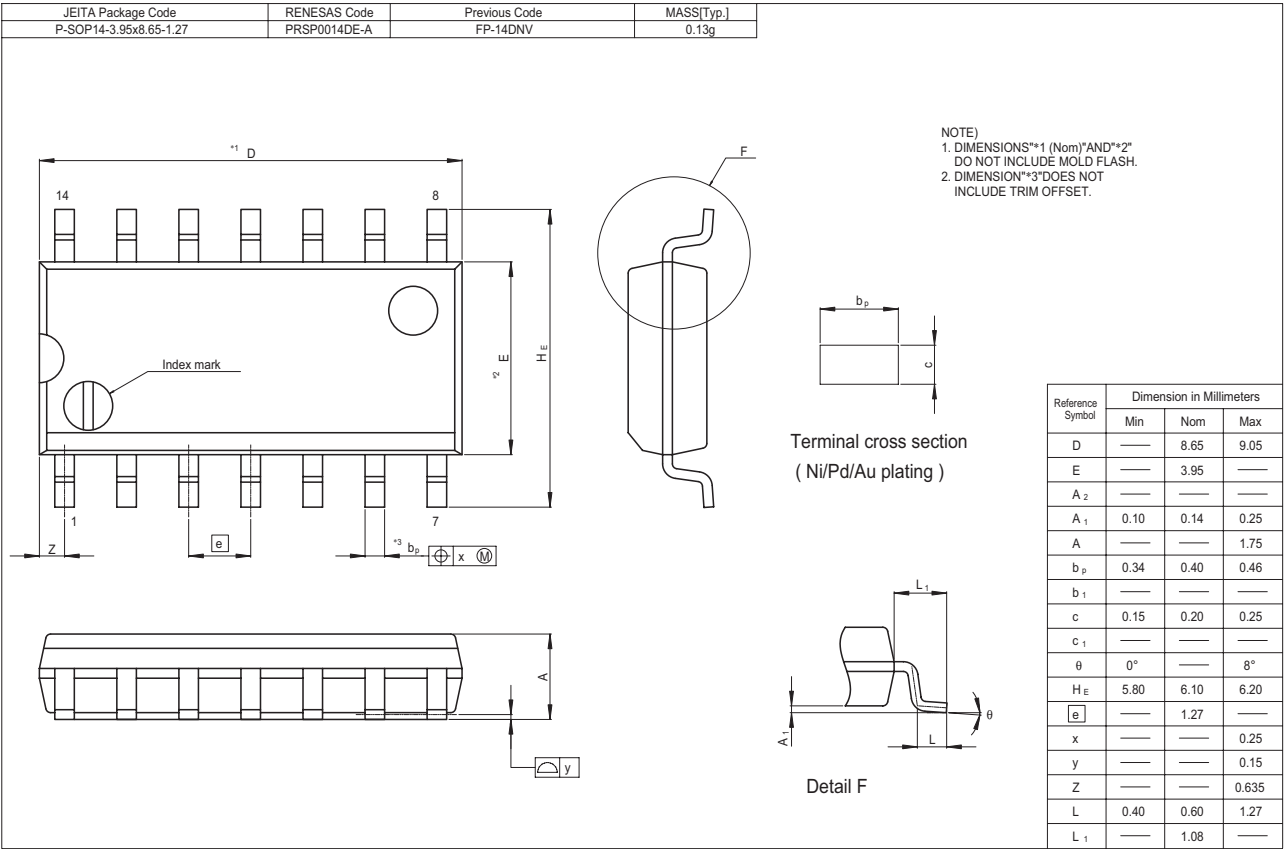
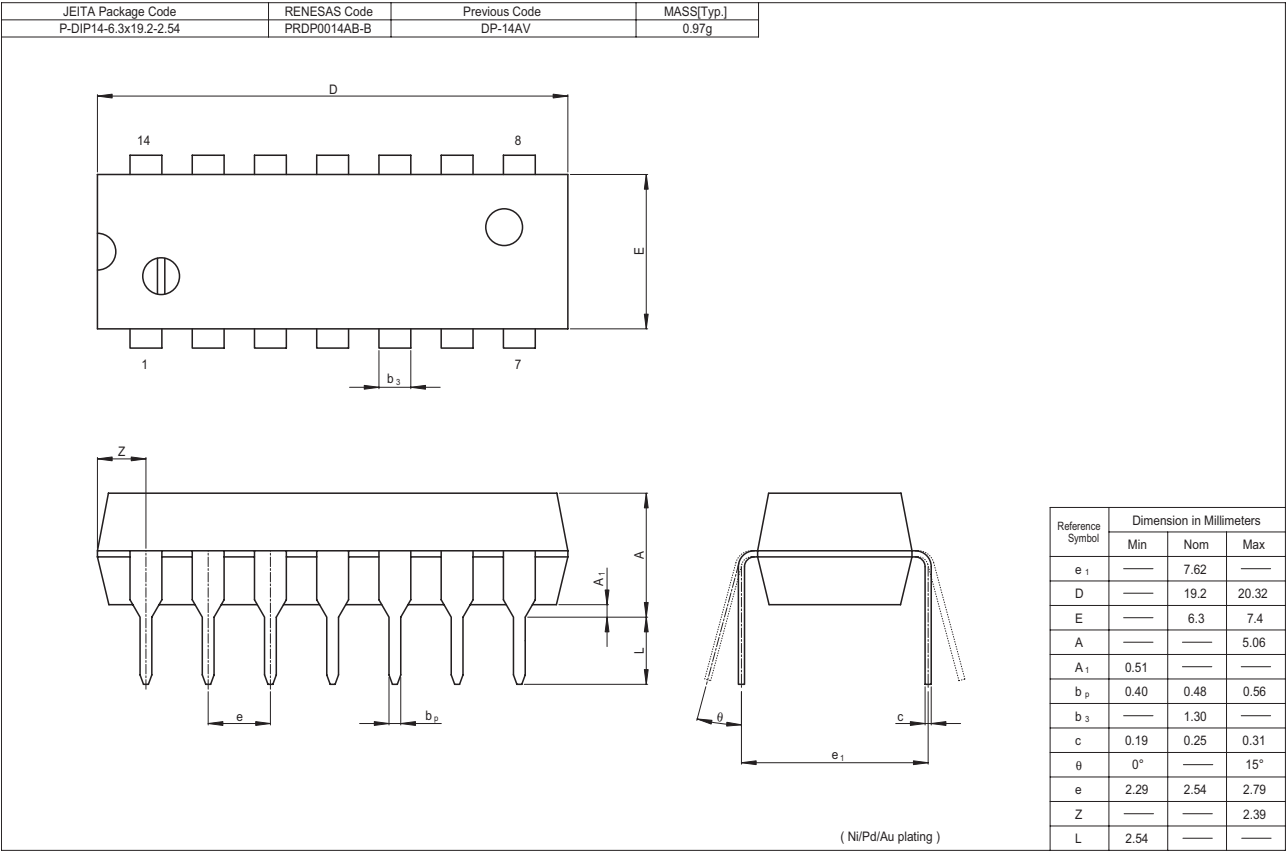
Waveforms

• Waveform – 1

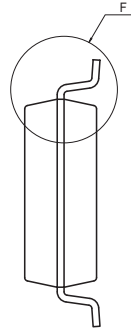
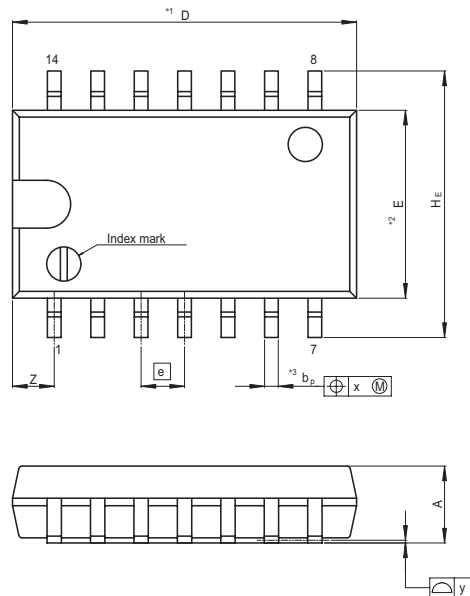


Notes: 1. Input waveform: $PRR \leq 1 \text{ MHz}$, $Z_o = 50 \Omega$, $t_r \leq 6 \text{ ns}$, $t_f \leq 6 \text{ ns}$
 2. The output are measured one at a time with one transition per measurement.

Package Dimensions 供应商

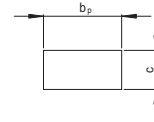


Previous Code	MASS[Typ.]
FP-14DAV	0.23g

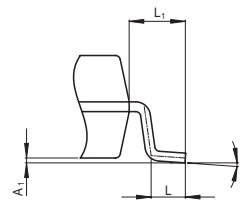


NOTE)

1. DIMENSIONS**1 (Nom)"AND**2"
DO NOT INCLUDE MOLD FLASH.
2. DIMENSION**3"DOES NOT
INCLUDE TRIM OFFSET.



Terminal cross section
(Ni/Pd/Au plating)



Detail F

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	—	10.06	10.5
E	—	5.50	—
A ₂	—	—	—
A ₁	0.00	0.10	0.20
A	—	—	2.20
b _p	0.34	0.40	0.46
b ₁	—	—	—
c	0.15	0.20	0.25
c ₁	—	—	—
θ	0°	—	8°
H _E	7.50	7.80	8.00
e	—	1.27	—
x	—	—	0.12
y	—	—	0.15
Z	—	—	1.42
L	0.50	0.70	0.90
L ₁	—	1.15	—

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